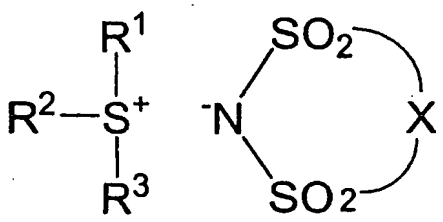
CLAIMS

1. A photoresist composition comprising:

(A) a polymer component comprising an alkaline-soluble constitutional unit that contains an aliphatic cyclic group having both (i) a fluorine atom or a fluorinated alkyl group and (ii) an alcoholic hydroxide group, the alkaline solubility of the polymer component being changeable by action of an acid; and

(B) an acid generating component, capable of generating an acid by way of exposure, that contains at least a sulfonium compound expressed by the general formula (1) below:



(1)

wherein, in the formula (1), X represents a C2 to C6 alkylene group of which at least a hydrogen atom is substituted by fluorine atom; R^1 to R^3 represent, independently of each other, an aryl or alkyl group; and at least one of R^1 to R^3 represents an aryl group.

2. A photoresist composition according to claim 1, further comprising a nitrogen-containing organic compound.

3. A photoresist composition according to claim 1, further comprising an organic carboxylic acid, or a phosphorous oxo

acid or derivative thereof.

4. A method of forming a resist pattern, comprising:

coating the photoresist composition according to claim 1 on a substrate to form a resist film,

selectively exposing the resist film, and

heating and developing the resist film after exposure to form a resist pattern.

5. A method of forming a resist pattern according to claim 4, wherein a SiON film is provided on the substrate.